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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

#### Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	55296
Number of I/O	178
Number of Gates	400000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/a3p400-1fgg256">https://www.e-xfl.com/product-detail/microchip-technology/a3p400-1fgg256</a>

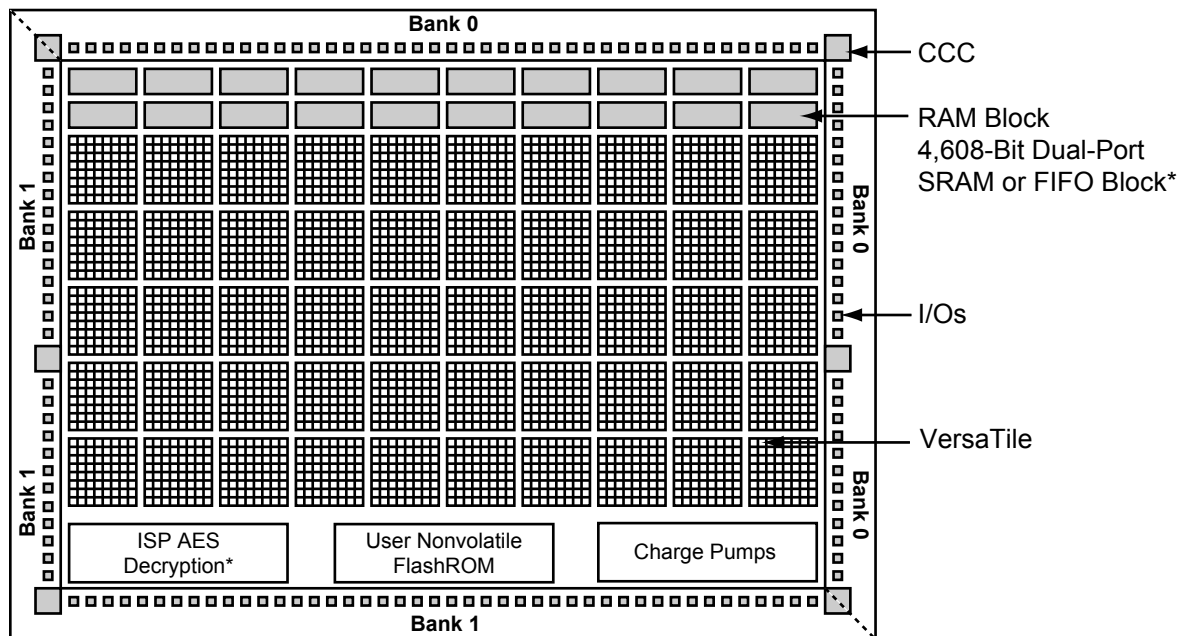
## Advanced Flash Technology

The ProASIC3 family offers many benefits, including nonvolatility and reprogrammability through an advanced flash-based, 130-nm LVC MOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

## Advanced Architecture

The proprietary ProASIC3 architecture provides granularity comparable to standard-cell ASICs. The ProASIC3 device consists of five distinct and programmable architectural features (Figure 1-1 and Figure 1-2 on page 1-4):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory†
- Extensive CCCs and PLLs†
- Advanced I/O structure



Note: \*Not supported by A3P015 and A3P030 devices

Figure 1-1 • ProASIC3 Device Architecture Overview with Two I/O Banks (A3P015, A3P030, A3P060, and A3P125)

† The A3P015 and A3P030 do not support PLL or SRAM.

## 2 – ProASIC3 DC and Switching Characteristics

### General Specifications

#### Operating Conditions

Stresses beyond those listed in [Table 2-1](#) may cause permanent damage to the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Absolute Maximum Ratings are stress ratings only; functional operation of the device at these or any other conditions beyond those listed under the Recommended Operating Conditions specified in [Table 2-2](#) on [page 2-2](#) is not implied.

**Table 2-1 • Absolute Maximum Ratings**

Symbol	Parameter	Limits	Units
VCC	DC core supply voltage	–0.3 to 1.65	V
VJTAG	JTAG DC voltage	–0.3 to 3.75	V
VPUMP	Programming voltage	–0.3 to 3.75	V
VCCPLL	Analog power supply (PLL)	–0.3 to 1.65	V
VCCI	DC I/O output buffer supply voltage	–0.3 to 3.75	V
VMV	DC I/O input buffer supply voltage	–0.3 to 3.75	V
VI	I/O input voltage	–0.3 V to 3.6 V (when I/O hot insertion mode is enabled) –0.3 V to (VCCI + 1 V) or 3.6 V, whichever voltage is lower (when I/O hot-insertion mode is disabled)	V
T <sub>STG</sub> <sup>2</sup>	Storage temperature	–65 to +150	°C
T <sub>J</sub> <sup>2</sup>	Junction temperature	+125	°C

**Notes:**

1. The device should be operated within the limits specified by the datasheet. During transitions, the input signal may undershoot or overshoot according to the limits shown in [Table 2-4](#) on [page 2-3](#).
2. VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on [page 3-1](#) for further information.
3. For flash programming and retention maximum limits, refer to [Table 2-3](#) on [page 2-3](#), and for recommended operating limits, refer to [Table 2-2](#) on [page 2-2](#).

### RAM Contribution— $P_{\text{MEMORY}}$

$$P_{\text{MEMORY}} = P_{\text{AC11}} * N_{\text{BLOCKS}} * F_{\text{READ-CLOCK}} * \beta_2 + P_{\text{AC12}} * N_{\text{BLOCK}} * F_{\text{WRITE-CLOCK}} * \beta_3$$

$N_{\text{BLOCKS}}$  is the number of RAM blocks used in the design.

$F_{\text{READ-CLOCK}}$  is the memory read clock frequency.

$\beta_2$  is the RAM enable rate for read operations.

$F_{\text{WRITE-CLOCK}}$  is the memory write clock frequency.

$\beta_3$  is the RAM enable rate for write operations—guidelines are provided in [Table 2-17 on page 2-14](#).

### PLL Contribution— $P_{\text{PLL}}$

$$P_{\text{PLL}} = P_{\text{DC4}} + P_{\text{AC13}} * F_{\text{CLKOUT}}$$

$F_{\text{CLKOUT}}$  is the output clock frequency.<sup>1</sup>

## Guidelines

### Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that this net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100% because all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
  - Bit 0 (LSB) = 100%
  - Bit 1 = 50%
  - Bit 2 = 25%
  - ...
  - Bit 7 (MSB) = 0.78125%
  - Average toggle rate = (100% + 50% + 25% + 12.5% + ... + 0.78125%) / 8

### Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

**Table 2-16 • Toggle Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
$\alpha_1$	Toggle rate of VersaTile outputs	10%
$\alpha_2$	I/O buffer toggle rate	10%

**Table 2-17 • Enable Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
$\beta_1$	I/O output buffer enable rate	100%
$\beta_2$	RAM enable rate for read operations	12.5%
$\beta_3$	RAM enable rate for write operations	12.5%

1. The PLL dynamic contribution depends on the input clock frequency, the number of output clock signals generated by the PLL, and the frequency of each output clock. If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution ( $P_{\text{AC14}} * F_{\text{CLKOUT}}$  product) to the total PLL contribution.

**Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings**  
 –2 Speed Grade, Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst Case VCC = 1.425 V,  
 Worst-Case VCCI (per standard)  
 Standard Plus I/O Banks

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option <sup>1</sup>	Slew Rate	Capacitive Load (pF)	External Resistor	$t_{\text{DOUT}}$ (ns)	$t_{\text{DP}}$ (ns)	$t_{\text{DIN}}$ (ns)	$t_{\text{PY}}$ (ns)	$t_{\text{EOUT}}$ (ns)	$t_{\text{ZL}}$ (ns)	$t_{\text{ZH}}$ (ns)	$t_{\text{LZ}}$ (ns)	$t_{\text{HZ}}$ (ns)	$t_{\text{ZLS}}$ (ns)	$t_{\text{ZHS}}$ (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	12 mA	High	35	–	0.45	2.36	0.03	0.75	0.32	2.40	1.93	2.08	2.41	4.07	3.60	ns
3.3 V LVCMOS Wide Range <sup>2</sup>	100 $\mu\text{A}$	12 mA	High	35	–	0.45	3.65	0.03	1.14	0.32	3.65	2.93	3.22	3.72	6.18	5.46	ns
2.5 V LVCMOS	12 mA	12 mA	High	35	–	0.45	2.39	0.03	0.97	0.32	2.44	2.35	2.11	2.32	4.11	4.02	ns
1.8 V LVCMOS	8 mA	8 mA	High	35	–	0.45	3.03	0.03	0.90	0.32	2.87	3.03	2.19	2.32	4.54	4.70	ns
1.5 V LVCMOS	4 mA	4 mA	High	35	–	0.45	3.61	0.03	1.06	0.32	3.35	3.61	2.26	2.34	5.02	5.28	ns
3.3 V PCI	Per PCI spec	–	High	10	25 <sup>4</sup>	0.45	1.72	0.03	0.64	0.32	1.76	1.27	2.08	2.41	3.42	2.94	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25 <sup>4</sup>	0.45	1.72	0.03	0.62	0.32	1.76	1.27	2.08	2.41	3.42	2.94	ns

**Notes:**

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is  $\pm 100 \mu\text{A}$ . Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.
4. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See [Figure 2-11 on page 2-64](#) for connectivity. This resistor is not required during normal operation.

**Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings**  
 –2 Speed Grade, Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst Case  $V_{CC} = 1.425\text{ V}$ ,  
 Worst-Case  $V_{CCI}$  (per standard)  
 Standard I/O Banks

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option <sup>1</sup>	Slew Rate	Capacitive Load (pF)	External Resistor	$t_{DOUT}$ (ns)	$t_{DP}$ (ns)	$t_{DIN}$ (ns)	$t_{PY}$ (ns)	$t_{EOUT}$ (ns)	$t_{ZL}$ (ns)	$t_{ZH}$ (ns)	$t_{LZ}$ (ns)	$t_{HZ}$ (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	8 mA	8 mA	High	35	–	0.45	3.29	0.03	0.75	0.32	3.36	2.80	1.79	2.01	ns
3.3 V LVCMOS Wide Range <sup>2</sup>	100 $\mu\text{A}$	8 mA	High	35	–	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns
2.5 V LVCMOS	8 mA	8 mA	High	35	–	0.45	3.56	0.03	0.96	0.32	3.40	3.56	1.78	1.91	ns
1.8 V LVCMOS	4 mA	4 mA	High	35	–	0.45	4.74	0.03	0.90	0.32	4.02	4.74	1.80	1.85	ns
1.5 V LVCMOS	2 mA	2 mA	High	35	–	0.45	5.71	0.03	1.06	0.32	4.71	5.71	1.83	1.83	ns

**Notes:**

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is  $\pm 100\ \mu\text{A}$ . Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-52 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 3.0\text{ V}$**   
**Applicable to Standard Plus I/O Banks**

Drive Strength	Equiv. Software Default Drive Strength Option <sup>1</sup>	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
100 $\mu\text{A}$	2 mA	Std.	0.60	11.14	0.04	1.52	0.43	11.14	9.54	3.51	3.61	14.53	12.94	ns
		-1	0.51	9.48	0.04	1.29	0.36	9.48	8.12	2.99	3.07	12.36	11.00	ns
		-2	0.45	8.32	0.03	1.14	0.32	8.32	7.13	2.62	2.70	10.85	9.66	ns
100 $\mu\text{A}$	4 mA	Std.	0.60	6.96	0.04	1.52	0.43	6.96	5.79	3.99	4.45	10.35	9.19	ns
		-1	0.51	5.92	0.04	1.29	0.36	5.92	4.93	3.39	3.78	8.81	7.82	ns
		-2	0.45	5.20	0.03	1.14	0.32	5.20	4.33	2.98	3.32	7.73	6.86	ns
100 $\mu\text{A}$	6 mA	Std.	0.60	6.96	0.04	1.52	0.43	6.96	5.79	3.99	4.45	10.35	9.19	ns
		-1	0.51	5.92	0.04	1.29	0.36	5.92	4.93	3.39	3.78	8.81	7.82	ns
		-2	0.45	5.20	0.03	1.14	0.32	5.20	4.33	2.98	3.32	7.73	6.86	ns
100 $\mu\text{A}$	8 mA	Std.	0.60	4.89	0.04	1.52	0.43	4.89	3.92	4.31	4.98	8.28	7.32	ns
		-1	0.51	4.16	0.04	1.29	0.36	4.16	3.34	3.67	4.24	7.04	6.22	ns
		-2	0.45	3.65	0.03	1.14	0.32	3.65	2.93	3.22	3.72	6.18	5.46	ns
100 $\mu\text{A}$	16 mA	Std.	0.60	4.89	0.04	1.52	0.43	4.89	3.92	4.31	4.98	8.28	7.32	ns
		-1	0.51	4.16	0.04	1.29	0.36	4.16	3.34	3.67	4.24	7.04	6.22	ns
		-2	0.45	3.65	0.03	1.14	0.32	3.65	2.93	3.22	3.72	6.18	5.46	ns

**Notes:**

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is  $\pm 100\ \mu\text{A}$ . Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. Software default selection highlighted in gray.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-72 • 1.8 V LVC MOS High Slew**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 1.7\text{ V}$**   
**Applicable to Standard Plus I/O Banks**

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
2 mA	Std.	0.66	11.33	0.04	1.20	0.43	8.72	11.33	2.24	1.52	10.96	13.57	ns
	-1	0.56	9.64	0.04	1.02	0.36	7.42	9.64	1.91	1.29	9.32	11.54	ns
	-2	0.49	8.46	0.03	0.90	0.32	6.51	8.46	1.68	1.14	8.18	10.13	ns
4 mA	Std.	0.66	6.48	0.04	1.20	0.43	5.48	6.48	2.65	2.60	7.72	8.72	ns
	-1	0.56	5.51	0.04	1.02	0.36	4.66	5.51	2.25	2.21	6.56	7.42	ns
	-2	0.49	4.84	0.03	0.90	0.32	4.09	4.84	1.98	1.94	5.76	6.51	ns
6 mA	Std.	0.66	4.06	0.04	1.20	0.43	3.84	4.06	2.93	3.10	6.07	6.30	ns
	-1	0.56	3.45	0.04	1.02	0.36	3.27	3.45	2.49	2.64	5.17	5.36	ns
	-2	0.49	3.03	0.03	0.90	0.32	2.87	3.03	2.19	2.32	4.54	4.70	ns
8 mA	Std.	0.66	4.06	0.04	1.20	0.43	3.84	4.06	2.93	3.10	6.07	6.30	ns
	-1	0.56	3.45	0.04	1.02	0.36	3.27	3.45	2.49	2.64	5.17	5.36	ns
	-2	0.49	3.03	0.03	0.90	0.32	2.87	3.03	2.19	2.32	4.54	4.70	ns

**Notes:**

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.



**Table 2-81 • 1.5 V LVCMOS Low Slew**

Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V  
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
2 mA	Std.	0.66	12.78	0.04	1.44	0.43	12.81	12.78	3.40	2.64	15.05	15.02	ns
	-1	0.56	10.87	0.04	1.22	0.36	10.90	10.87	2.89	2.25	12.80	12.78	ns
	-2	0.49	9.55	0.03	1.07	0.32	9.57	9.55	2.54	1.97	11.24	11.22	ns
4 mA	Std.	0.66	10.01	0.04	1.44	0.43	10.19	9.55	3.75	3.27	12.43	11.78	ns
	-1	0.56	8.51	0.04	1.22	0.36	8.67	8.12	3.19	2.78	10.57	10.02	ns
	-2	0.49	7.47	0.03	1.07	0.32	7.61	7.13	2.80	2.44	9.28	8.80	ns
6 mA	Std.	0.66	9.33	0.04	1.44	0.43	9.51	8.89	3.83	3.43	11.74	11.13	ns
	-1	0.56	7.94	0.04	1.22	0.36	8.09	7.56	3.26	2.92	9.99	9.47	ns
	-2	0.49	6.97	0.03	1.07	0.32	7.10	6.64	2.86	2.56	8.77	8.31	ns
8 mA	Std.	0.66	8.91	0.04	1.44	0.43	9.07	8.89	3.95	4.05	11.31	11.13	ns
	-1	0.56	7.58	0.04	1.22	0.36	7.72	7.57	3.36	3.44	9.62	9.47	ns
	-2	0.49	6.65	0.03	1.07	0.32	6.78	6.64	2.95	3.02	8.45	8.31	ns
12 mA	Std.	0.66	8.91	0.04	1.44	0.43	9.07	8.89	3.95	4.05	11.31	11.13	ns
	-1	0.56	7.58	0.04	1.22	0.36	7.72	7.57	3.36	3.44	9.62	9.47	ns
	-2	0.49	6.65	0.03	1.07	0.32	6.78	6.64	2.95	3.02	8.45	8.31	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

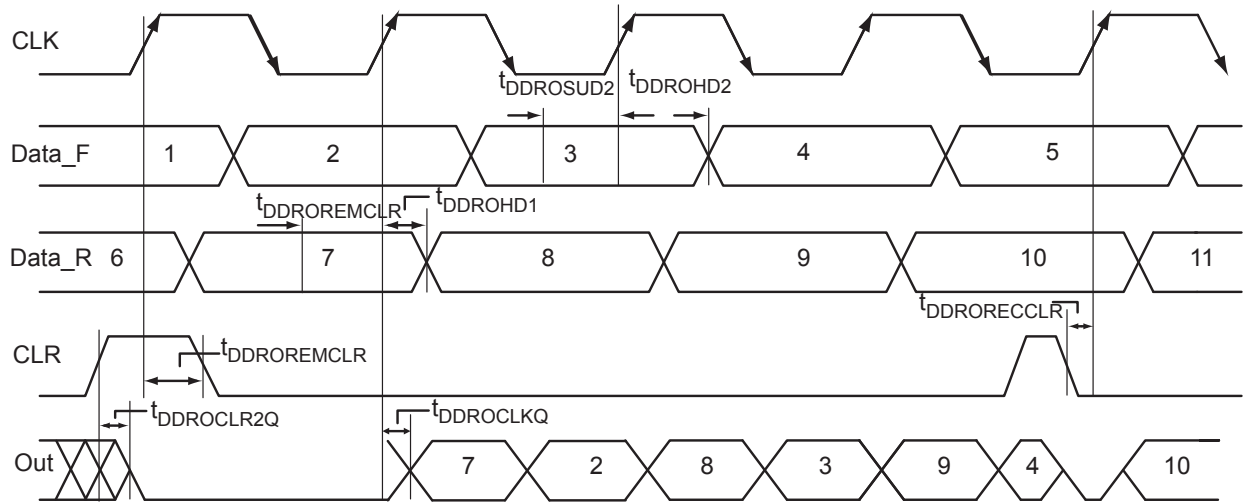
**Table 2-82 • 1.5 V LVCMOS High Slew**

Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V  
 Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
2 mA	Std.	0.66	7.83	0.04	1.42	0.43	6.42	7.83	2.71	2.55	8.65	10.07	ns
	-1	0.56	6.66	0.04	1.21	0.36	5.46	6.66	2.31	2.17	7.36	8.56	ns
	-2	0.49	5.85	0.03	1.06	0.32	4.79	5.85	2.02	1.90	6.46	7.52	ns
4 mA	Std.	0.66	4.84	0.04	1.42	0.43	4.49	4.84	3.03	3.13	6.72	7.08	ns
	-1	0.56	4.12	0.04	1.21	0.36	3.82	4.12	2.58	2.66	5.72	6.02	ns
	-2	0.49	3.61	0.03	1.06	0.32	3.35	3.61	2.26	2.34	5.02	5.28	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.



**Figure 2-23 • Output DDR Timing Diagram**

**Timing Characteristics**

**Table 2-104 • Output DDR Propagation Delays**

Commercial-Case Conditions:  $T_j = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
$t_{\text{DDROCLKQ}}$	Clock-to-Out of DDR for Output DDR	0.70	0.80	0.94	ns
$t_{\text{DDROSUD1}}$	Data_F Data Setup for Output DDR	0.38	0.43	0.51	ns
$t_{\text{DDROSUD2}}$	Data_R Data Setup for Output DDR	0.38	0.43	0.51	ns
$t_{\text{DDROHD1}}$	Data_F Data Hold for Output DDR	0.00	0.00	0.00	ns
$t_{\text{DDROHD2}}$	Data_R Data Hold for Output DDR	0.00	0.00	0.00	ns
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out for Output DDR	0.80	0.91	1.07	ns
$t_{\text{DDROEMCLR}}$	Asynchronous Clear Removal Time for Output DDR	0.00	0.00	0.00	ns
$t_{\text{DDROECCLR}}$	Asynchronous Clear Recovery Time for Output DDR	0.22	0.25	0.30	ns
$t_{\text{DDROWCLR1}}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.22	0.25	0.30	ns
$t_{\text{DDROCKMPWH}}$	Clock Minimum Pulse Width High for the Output DDR	0.36	0.41	0.48	ns
$t_{\text{DDROCKMPWL}}$	Clock Minimum Pulse Width Low for the Output DDR	0.32	0.37	0.43	ns
$F_{\text{DDOMAX}}$	Maximum Frequency for the Output DDR	350	309	263	MHz

*Note:* For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

**Table 2-113 • A3P600 Global Resource**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.425\text{ V}$**

Parameter	Description	-2		-1		Std.		Units
		Min. <sup>1</sup>	Max. <sup>2</sup>	Min. <sup>1</sup>	Max. <sup>2</sup>	Min. <sup>1</sup>	Max. <sup>2</sup>	
t <sub>RCKL</sub>	Input Low Delay for Global Clock	0.87	1.09	0.99	1.24	1.17	1.46	ns
t <sub>RCKH</sub>	Input High Delay for Global Clock	0.86	1.11	0.98	1.27	1.15	1.49	ns
t <sub>RCKMPWH</sub>	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
t <sub>RCKMPWL</sub>	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t <sub>RCKSW</sub>	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

**Notes:**

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-114 • A3P1000 Global Resource**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.425\text{ V}$**

Parameter	Description	-2		-1		Std.		Units
		Min. <sup>1</sup>	Max. <sup>2</sup>	Min. <sup>1</sup>	Max. <sup>2</sup>	Min. <sup>1</sup>	Max. <sup>2</sup>	
t <sub>RCKL</sub>	Input Low Delay for Global Clock	0.94	1.16	1.07	1.32	1.26	1.55	ns
t <sub>RCKH</sub>	Input High Delay for Global Clock	0.93	1.19	1.06	1.35	1.24	1.59	ns
t <sub>RCKMPWH</sub>	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
t <sub>RCKMPWL</sub>	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t <sub>RCKSW</sub>	Maximum Skew for Global Clock		0.26		0.29		0.35	ns

**Notes:**

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

### **VJTAG**                      **JTAG Supply Voltage**

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design.

If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

It should be noted that VCC is required to be powered for JTAG operation; VJTAG alone is insufficient. If a device is in a JTAG chain of interconnected boards, the board containing the device can be powered down, provided both VJTAG and VCC to the part remain powered; otherwise, JTAG signals will not be able to transition the device, even in bypass mode.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

### **VPUMP**                      **Programming Supply Voltage**

ProASIC3 devices support single-voltage ISP of the configuration flash and FlashROM. For programming, VPUMP should be 3.3 V nominal. During normal device operation, VPUMP can be left floating or can be tied (pulled up) to any voltage between 0 V and the VPUMP maximum. Programming power supply voltage (VPUMP) range is listed in [Table 2-2 on page 2-2](#).

When the VPUMP pin is tied to ground, it will shut off the charge pump circuitry, resulting in no sources of oscillation from the charge pump circuitry.

For proper programming, 0.01  $\mu$ F and 0.33  $\mu$ F capacitors (both rated at 16 V) are to be connected in parallel across VPUMP and GND, and positioned as close to the FPGA pins as possible.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

## **User Pins**

### **I/O**                              **User Input/Output**

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Input and output signal levels are compatible with the I/O standard selected.

During programming, I/Os become tristated and weakly pulled up to  $V_{CCI}$ . With  $V_{CCI}$ , VMV, and  $V_{CC}$  supplies continuously powered up, when the device transitions from programming to operating mode, the I/Os are instantly configured to the desired user configuration.

Unused I/Os are configured as follows:

- Output buffer is disabled (with tristate value of high impedance)
- Input buffer is disabled (with tristate value of high impedance)
- Weak pull-up is programmed

### **GL**                              **Globals**

GL I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities. Unused GL pins are configured as inputs with pull-up resistors.

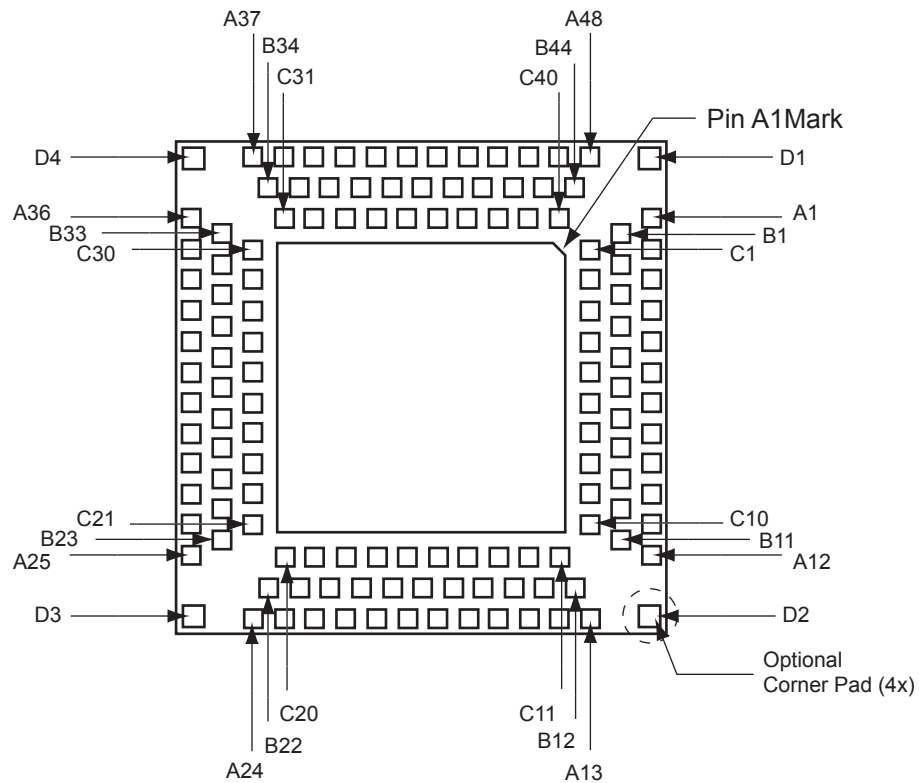
See more detailed descriptions of global I/O connectivity in the "Clock Conditioning Circuits in IGLOO and ProASIC3 Devices" chapter of the [ProASIC3 FPGA Fabric User's Guide](#). All inputs labeled GC/GF are direct inputs into the quadrant clocks. For example, if GAA0 is used for an input, GAA1 and GAA2 are no longer available for input to the quadrant globals. All inputs labeled GC/GF are direct inputs into the chip-level globals, and the rest are connected to the quadrant globals. The inputs to the global network are multiplexed, and only one input can be used as a global input.

Refer to the I/O Structure section of the handbook for the device you are using for an explanation of the naming of global pins.

### **FF**                              **Flash\*Freeze Mode Activation Pin**

Flash\*Freeze is available on IGLOO, ProASIC3L, and RT ProASIC3 devices. It is not supported on ProASIC3/E devices. The FF pin is a dedicated input pin used to enter and exit Flash\*Freeze mode. The FF pin is active-low, has the same characteristics as a single-ended I/O, and must meet the maximum rise and fall times. When Flash\*Freeze

## QN132 – Bottom View



### Notes:

1. The die attach paddle center of the package is tied to ground (GND).
2. Option corner pads come with this device and package combination. It is optional to tie them to ground or leave them floating.
3. The QN132 package is discontinued and is not available for ProASIC3 devices.
4. For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

VQ100	
Pin Number	A3P060 Function
1	GND
2	GAA2/IO51RSB1
3	IO52RSB1
4	GAB2/IO53RSB1
5	IO95RSB1
6	GAC2/IO94RSB1
7	IO93RSB1
8	IO92RSB1
9	GND
10	GFB1/IO87RSB1
11	GFB0/IO86RSB1
12	VCOMPLF
13	GFA0/IO85RSB1
14	VCCPLF
15	GFA1/IO84RSB1
16	GFA2/IO83RSB1
17	VCC
18	VCCIB1
19	GEC1/IO77RSB1
20	GEB1/IO75RSB1
21	GEB0/IO74RSB1
22	GEA1/IO73RSB1
23	GEA0/IO72RSB1
24	VMV1
25	GNDQ
26	GEA2/IO71RSB1
27	GEB2/IO70RSB1
28	GEC2/IO69RSB1
29	IO68RSB1
30	IO67RSB1
31	IO66RSB1
32	IO65RSB1
33	IO64RSB1
34	IO63RSB1
35	IO62RSB1
36	IO61RSB1

VQ100	
Pin Number	A3P060 Function
37	VCC
38	GND
39	VCCIB1
40	IO60RSB1
41	IO59RSB1
42	IO58RSB1
43	IO57RSB1
44	GDC2/IO56RSB1
45	GDB2/IO55RSB1
46	GDA2/IO54RSB1
47	TCK
48	TDI
49	TMS
50	VMV1
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO49RSB0
58	GDC0/IO46RSB0
59	GDC1/IO45RSB0
60	GCC2/IO43RSB0
61	GCB2/IO42RSB0
62	GCA0/IO40RSB0
63	GCA1/IO39RSB0
64	GCC0/IO36RSB0
65	GCC1/IO35RSB0
66	VCCIB0
67	GND
68	VCC
69	IO31RSB0
70	GBC2/IO29RSB0
71	GBB2/IO27RSB0
72	IO26RSB0

VQ100	
Pin Number	A3P060 Function
73	GBA2/IO25RSB0
74	VMV0
75	GNDQ
76	GBA1/IO24RSB0
77	GBA0/IO23RSB0
78	GBB1/IO22RSB0
79	GBB0/IO21RSB0
80	GBC1/IO20RSB0
81	GBC0/IO19RSB0
82	IO18RSB0
83	IO17RSB0
84	IO15RSB0
85	IO13RSB0
86	IO11RSB0
87	VCCIB0
88	GND
89	VCC
90	IO10RSB0
91	IO09RSB0
92	IO08RSB0
93	GAC1/IO07RSB0
94	GAC0/IO06RSB0
95	GAB1/IO05RSB0
96	GAB0/IO04RSB0
97	GAA1/IO03RSB0
98	GAA0/IO02RSB0
99	IO01RSB0
100	IO00RSB0

TQ144	
Pin Number	A3P125 Function
1	GAA2/IO67RSB1
2	IO68RSB1
3	GAB2/IO69RSB1
4	IO132RSB1
5	GAC2/IO131RSB1
6	IO130RSB1
7	IO129RSB1
8	IO128RSB1
9	VCC
10	GND
11	VCCIB1
12	IO127RSB1
13	GFC1/IO126RSB1
14	GFC0/IO125RSB1
15	GFB1/IO124RSB1
16	GFB0/IO123RSB1
17	VCOMPLF
18	GFA0/IO122RSB1
19	VCCPLF
20	GFA1/IO121RSB1
21	GFA2/IO120RSB1
22	GFB2/IO119RSB1
23	GFC2/IO118RSB1
24	IO117RSB1
25	IO116RSB1
26	IO115RSB1
27	GND
28	VCCIB1
29	GEC1/IO112RSB1
30	GEC0/IO111RSB1
31	GEB1/IO110RSB1
32	GEB0/IO109RSB1
33	GEA1/IO108RSB1
34	GEA0/IO107RSB1
35	VMV1
36	GNDQ

TQ144	
Pin Number	A3P125 Function
37	NC
38	GEA2/IO106RSB1
39	GEB2/IO105RSB1
40	GEC2/IO104RSB1
41	IO103RSB1
42	IO102RSB1
43	IO101RSB1
44	IO100RSB1
45	VCC
46	GND
47	VCCIB1
48	IO99RSB1
49	IO97RSB1
50	IO95RSB1
51	IO93RSB1
52	IO92RSB1
53	IO90RSB1
54	IO88RSB1
55	IO86RSB1
56	IO84RSB1
57	IO83RSB1
58	IO82RSB1
59	IO81RSB1
60	IO80RSB1
61	IO79RSB1
62	VCC
63	GND
64	VCCIB1
65	GDC2/IO72RSB1
66	GDB2/IO71RSB1
67	GDA2/IO70RSB1
68	GNDQ
69	TCK
70	TDI
71	TMS
72	VMV1

TQ144	
Pin Number	A3P125 Function
73	VPUMP
74	NC
75	TDO
76	TRST
77	VJTAG
78	GDA0/IO66RSB0
79	GDB0/IO64RSB0
80	GDB1/IO63RSB0
81	VCCIB0
82	GND
83	IO60RSB0
84	GCC2/IO59RSB0
85	GCB2/IO58RSB0
86	GCA2/IO57RSB0
87	GCA0/IO56RSB0
88	GCA1/IO55RSB0
89	GCB0/IO54RSB0
90	GCB1/IO53RSB0
91	GCC0/IO52RSB0
92	GCC1/IO51RSB0
93	IO50RSB0
94	IO49RSB0
95	NC
96	NC
97	NC
98	VCCIB0
99	GND
100	VCC
101	IO47RSB0
102	GBC2/IO45RSB0
103	IO44RSB0
104	GBB2/IO43RSB0
105	IO42RSB0
106	GBA2/IO41RSB0
107	VMV0
108	GNDQ

TQ144	
Pin Number	A3P125 Function
109	GBA1/IO40RSB0
110	GBA0/IO39RSB0
111	GBB1/IO38RSB0
112	GBB0/IO37RSB0
113	GBC1/IO36RSB0
114	GBC0/IO35RSB0
115	IO34RSB0
116	IO33RSB0
117	VCCIB0
118	GND
119	VCC
120	IO29RSB0
121	IO28RSB0
122	IO27RSB0
123	IO25RSB0
124	IO23RSB0
125	IO21RSB0
126	IO19RSB0
127	IO17RSB0
128	IO16RSB0
129	IO14RSB0
130	IO12RSB0
131	IO10RSB0
132	IO08RSB0
133	IO06RSB0
134	VCCIB0
135	GND
136	VCC
137	GAC1/IO05RSB0
138	GAC0/IO04RSB0
139	GAB1/IO03RSB0
140	GAB0/IO02RSB0
141	GAA1/IO01RSB0
142	GAA0/IO00RSB0
143	GNDQ
144	VMV0



PQ208	
Pin Number	A3P250 Function
109	TRST
110	VJTAG
111	GDA0/IO60VDB1
112	GDA1/IO60UDB1
113	GDB0/IO59VDB1
114	GDB1/IO59UDB1
115	GDC0/IO58VDB1
116	GDC1/IO58UDB1
117	IO57VDB1
118	IO57UDB1
119	IO56NDB1
120	IO56PDB1
121	IO55RSB1
122	GND
123	VCCIB1
124	NC
125	NC
126	VCC
127	IO53NDB1
128	GCC2/IO53PDB1
129	GCB2/IO52PSB1
130	GND
131	GCA2/IO51PSB1
132	GCA1/IO50PDB1
133	GCA0/IO50NDB1
134	GCB0/IO49NDB1
135	GCB1/IO49PDB1
136	GCC0/IO48NDB1
137	GCC1/IO48PDB1
138	IO47NDB1
139	IO47PDB1
140	VCCIB1
141	GND
142	VCC
143	IO46RSB1
144	IO45NDB1

PQ208	
Pin Number	A3P250 Function
145	IO45PDB1
146	IO44NDB1
147	IO44PDB1
148	IO43NDB1
149	GBC2/IO43PDB1
150	IO42NDB1
151	GBB2/IO42PDB1
152	IO41NDB1
153	GBA2/IO41PDB1
154	VMV1
155	GNDQ
156	GND
157	NC
158	GBA1/IO40RSB0
159	GBA0/IO39RSB0
160	GBB1/IO38RSB0
161	GBB0/IO37RSB0
162	GND
163	GBC1/IO36RSB0
164	GBC0/IO35RSB0
165	IO34RSB0
166	IO33RSB0
167	IO32RSB0
168	IO31RSB0
169	IO30RSB0
170	VCCIB0
171	VCC
172	IO29RSB0
173	IO28RSB0
174	IO27RSB0
175	IO26RSB0
176	IO25RSB0
177	IO24RSB0
178	GND
179	IO23RSB0
180	IO22RSB0

PQ208	
Pin Number	A3P250 Function
181	IO21RSB0
182	IO20RSB0
183	IO19RSB0
184	IO18RSB0
185	IO17RSB0
186	VCCIB0
187	VCC
188	IO16RSB0
189	IO15RSB0
190	IO14RSB0
191	IO13RSB0
192	IO12RSB0
193	IO11RSB0
194	IO10RSB0
195	GND
196	IO09RSB0
197	IO08RSB0
198	IO07RSB0
199	IO06RSB0
200	VCCIB0
201	GAC1/IO05RSB0
202	GAC0/IO04RSB0
203	GAB1/IO03RSB0
204	GAB0/IO02RSB0
205	GAA1/IO01RSB0
206	GAA0/IO00RSB0
207	GNDQ
208	VMV0

PQ208	
Pin Number	A3P600 Function
109	TRST
110	VJTAG
111	GDA0/IO88NDB1
112	GDA1/IO88PDB1
113	GDB0/IO87NDB1
114	GDB1/IO87PDB1
115	GDC0/IO86NDB1
116	GDC1/IO86PDB1
117	IO84NDB1
118	IO84PDB1
119	IO82NDB1
120	IO82PDB1
121	IO81PSB1
122	GND
123	VCCIB1
124	IO77NDB1
125	IO77PDB1
126	NC
127	IO74NDB1
128	GCC2/IO74PDB1
129	GCB2/IO73PSB1
130	GND
131	GCA2/IO72PSB1
132	GCA1/IO71PDB1
133	GCA0/IO71NDB1
134	GCB0/IO70NDB1
135	GCB1/IO70PDB1
136	GCC0/IO69NDB1
137	GCC1/IO69PDB1
138	IO67NDB1
139	IO67PDB1
140	VCCIB1
141	GND
142	VCC
143	IO65PSB1
144	IO64NDB1

PQ208	
Pin Number	A3P600 Function
145	IO64PDB1
146	IO63NDB1
147	IO63PDB1
148	IO62NDB1
149	GBC2/IO62PDB1
150	IO61NDB1
151	GBB2/IO61PDB1
152	IO60NDB1
153	GBA2/IO60PDB1
154	VMV1
155	GNDQ
156	GND
157	VMV0
158	GBA1/IO59RSB0
159	GBA0/IO58RSB0
160	GBB1/IO57RSB0
161	GBB0/IO56RSB0
162	GND
163	GBC1/IO55RSB0
164	GBC0/IO54RSB0
165	IO52RSB0
166	IO50RSB0
167	IO48RSB0
168	IO46RSB0
169	IO44RSB0
170	VCCIB0
171	VCC
172	IO36RSB0
173	IO35RSB0
174	IO34RSB0
175	IO33RSB0
176	IO32RSB0
177	IO31RSB0
178	GND
179	IO29RSB0
180	IO28RSB0

PQ208	
Pin Number	A3P600 Function
181	IO27RSB0
182	IO26RSB0
183	IO25RSB0
184	IO24RSB0
185	IO23RSB0
186	VCCIB0
187	VCC
188	IO20RSB0
189	IO19RSB0
190	IO18RSB0
191	IO17RSB0
192	IO16RSB0
193	IO14RSB0
194	IO12RSB0
195	GND
196	IO10RSB0
197	IO09RSB0
198	IO08RSB0
199	IO07RSB0
200	VCCIB0
201	GAC1/IO05RSB0
202	GAC0/IO04RSB0
203	GAB1/IO03RSB0
204	GAB0/IO02RSB0
205	GAA1/IO01RSB0
206	GAA0/IO00RSB0
207	GNDQ
208	VMV0

FG484	
Pin Number	A3P1000 Function
A1	GND
A2	GND
A3	VCCIB0
A4	IO07RSB0
A5	IO09RSB0
A6	IO13RSB0
A7	IO18RSB0
A8	IO20RSB0
A9	IO26RSB0
A10	IO32RSB0
A11	IO40RSB0
A12	IO41RSB0
A13	IO53RSB0
A14	IO59RSB0
A15	IO64RSB0
A16	IO65RSB0
A17	IO67RSB0
A18	IO69RSB0
A19	NC
A20	VCCIB0
A21	GND
A22	GND
B1	GND
B2	VCCIB3
B3	NC
B4	IO06RSB0
B5	IO08RSB0
B6	IO12RSB0
B7	IO15RSB0
B8	IO19RSB0
B9	IO24RSB0
B10	IO31RSB0
B11	IO39RSB0
B12	IO48RSB0
B13	IO54RSB0
B14	IO58RSB0

FG484	
Pin Number	A3P1000 Function
B15	IO63RSB0
B16	IO66RSB0
B17	IO68RSB0
B18	IO70RSB0
B19	NC
B20	NC
B21	VCCIB1
B22	GND
C1	VCCIB3
C2	IO220PDB3
C3	NC
C4	NC
C5	GND
C6	IO10RSB0
C7	IO14RSB0
C8	VCC
C9	VCC
C10	IO30RSB0
C11	IO37RSB0
C12	IO43RSB0
C13	NC
C14	VCC
C15	VCC
C16	NC
C17	NC
C18	GND
C19	NC
C20	NC
C21	NC
C22	VCCIB1
D1	IO219PDB3
D2	IO220NDB3
D3	NC
D4	GND
D5	GAA0/IO00RSB0
D6	GAA1/IO01RSB0

FG484	
Pin Number	A3P1000 Function
D7	GAB0/IO02RSB0
D8	IO16RSB0
D9	IO22RSB0
D10	IO28RSB0
D11	IO35RSB0
D12	IO45RSB0
D13	IO50RSB0
D14	IO55RSB0
D15	IO61RSB0
D16	GBB1/IO75RSB0
D17	GBA0/IO76RSB0
D18	GBA1/IO77RSB0
D19	GND
D20	NC
D21	NC
D22	NC
E1	IO219NDB3
E2	NC
E3	GND
E4	GAB2/IO224PDB3
E5	GAA2/IO225PDB3
E6	GNDQ
E7	GAB1/IO03RSB0
E8	IO17RSB0
E9	IO21RSB0
E10	IO27RSB0
E11	IO34RSB0
E12	IO44RSB0
E13	IO51RSB0
E14	IO57RSB0
E15	GBC1/IO73RSB0
E16	GBB0/IO74RSB0
E17	IO71RSB0
E18	GBA2/IO78PDB1
E19	IO81PDB1
E20	GND

Revision	Changes	Page
Revision 13 (January 2013)	The "ProASIC3 Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43104).	1-IV
	Added a note to Table 2-2 • Recommended Operating Conditions 1 (SAR 43644): The programming temperature range supported is $T_{\text{ambient}} = 0^{\circ}\text{C}$ to $85^{\circ}\text{C}$ .	2-2
	The note in Table 2-115 • ProASIC3 CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42569).	2-90
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 40284). Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 12 (September 2012)	The Security section was modified to clarify that Microsemi does not support read-back of programmed data.	1-1
	Added a Note stating "VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information" to Table 2-1 • Absolute Maximum Ratings and Table 2-2 • Recommended Operating Conditions 1 (SAR 38321).	2-1 2-2
	Table 2-35 • Duration of Short Circuit Event Before Failure was revised to change the maximum temperature from $110^{\circ}\text{C}$ to $100^{\circ}\text{C}$ , with an example of six months instead of three months (SAR 37933).	2-31
	In Table 2-93 • Minimum and Maximum DC Input and Output Levels, VIL and VIH were revised so that the maximum is 3.6 V for all listed values of VCCI (SAR 28549).	2-68
	Figure 2-37 • FIFO Read and Figure 2-38 • FIFO Write are new (SAR 28371).	2-99
	The following sentence was removed from the "VMVx I/O Supply Voltage (quiet)" section in the "Pin Descriptions" chapter: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with "Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks" (SAR 38321). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1

Revision	Changes	Page
Advance v0.6 (continued)	The "RESET" section was updated.	2-25
	The "WCLK and RCLK" section was updated.	2-25
	The "RESET" section was updated.	2-25
	The "RESET" section was updated.	2-27
	The "Introduction" of the "Advanced I/Os" section was updated.	2-28
	The "I/O Banks" section is new. This section explains the following types of I/Os: Advanced Standard+ Standard Table 2-12 • Automotive ProASIC3 Bank Types Definition and Differences is new. This table describes the standards listed above.	2-29
	PCI-X 3.3 V was added to the Compatible Standards for 3.3 V in Table 2-11 • VCCI Voltages and Compatible Standards	2-29
	Table 2-13 • ProASIC3 I/O Features was updated.	2-30
	The "Double Data Rate (DDR) Support" section was updated to include information concerning implementation of the feature.	2-32
	The "Electrostatic Discharge (ESD) Protection" section was updated to include testing information.	2-35
	Level 3 and 4 descriptions were updated in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices.	2-64
	The notes in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices were updated.	2-64
	The "Simultaneous Switching Outputs (SSOs) and Printed Circuit Board Layout" section is new.	2-41
	A footnote was added to Table 2-14 • Maximum I/O Frequency for Single-Ended and Differential I/Os in All Banks in Automotive ProASIC3 Devices (maximum drive strength and high slew selected).	2-30
	Table 2-18 • Automotive ProASIC3 I/O Attributes vs. I/O Standard Applications	2-45
	Table 2-50 • ProASIC3 Output Drive (OUT_DRIVE) for Standard I/O Bank Type (A3P030 device)	2-83
	Table 2-51 • ProASIC3 Output Drive for Standard+ I/O Bank Type was updated.	2-84
	Table 2-54 • ProASIC3 Output Drive for Advanced I/O Bank Type was updated.	2-84
	The "x" was updated in the "User I/O Naming Convention" section.	2-48
	The "VCC Core Supply Voltage" pin description was updated.	2-50
The "VMVx I/O Supply Voltage (quiet)" pin description was updated to include information concerning leaving the pin unconnected.	2-50	
The "VJTAG JTAG Supply Voltage" pin description was updated.	2-50	
The "VPUMP Programming Supply Voltage" pin description was updated to include information on what happens when the pin is tied to ground.	2-50	
The "I/O User Input/Output" pin description was updated to include information on what happens when the pin is unused.	2-50	
The "JTAG Pins" section was updated to include information on what happens when the pin is unused.	2-51	